

## FORMATION OF SILICON OXIDE COATING FILM

## FORMATION OF SILICON OXIDE COATING FILM

Patent Number: JP60065712  
Publication date: 1985-04-15  
Inventor(s): HAYAMA NORIYUKI; others: 03  
Applicant(s): TOSHIBA KK  
Requested Patent: ☐ JP60065712  
Application Number: JP19830172222 19830920  
Priority Number(s):  
IPC Classification: C01B33/113  
EC Classification:  
EC Classification:  
Equivalents:

### Abstract

**PURPOSE:** A substrate is coated with an organosilicon compound containing ultra- violet absorbing substances and sintered in an oxidative atmosphere as ultraviolet rays are irradiated to effect oxidation whereby good coating films of silicon oxide are formed at relatively low temperatures.

**CONSTITUTION:** A substrate is coated with an organosilicon compound containing an ultraviolet absorbing substance such as an organotitanium compound and placed in a heating furnace, then baked in an oxidative atmosphere at about 350 deg.C, as ultraviolet rays are irradiated to oxidize the organosilicon compound and form coating films of silicon oxide on the substrate. Thus, silicon oxide coating films used as optical interference films with high refractive index.